

# Yage Liu

## List of Publications by Year in descending order

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1937685  
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#	ARTICLE	IF	CITATIONS
1	Towards Surface Leakage Free High Fill-Factor Extended Wavelength InGaAs Focal-Plane Arrays. IEEE Journal of Quantum Electronics, 2019, 55, 1-8.	1.9	9
2	Surface Leakage Behaviors of $2.6\text{-}\mu\text{m}$ $\text{In}_{0.83}\text{Ga}_{0.17}\text{As}$ Photodetectors as a Function of Mesa Etching Depth. IEEE Journal of Quantum Electronics, 2020, 56, 1-6.	1.9	9
3	Dark current and $1/f$ noise characteristics of $\text{In}_{0.74}\text{Ga}_{0.26}\text{As}$ photodiode passivated by $\text{SiN}_x/\text{Al}_2\text{O}_3$ bilayer. Infrared Physics and Technology, 2020, 109, 103389.	2.9	6
4	$320\text{\AA}$ – $256\text{\AA}$ Extended Wavelength $\text{In}_x\text{Ga}_{1-x}\text{As}/\text{InP}$ Focal Plane Arrays: Dislocation Defect, Dark Signal and Noise. IEEE Journal of Selected Topics in Quantum Electronics, 2022, 28, 1-11.	2.9	6
5	High Temperature Behaviors of $1.25\text{-}\mu\text{m}$ Extended Wavelength $\text{In}_{0.7}\text{Ga}_{0.3}\text{As}$ Photodetectors on $\text{InP}$ Substrate. IEEE Journal of Quantum Electronics, 2021, 57, 1-7.	1.9	3
6	Dislocation Evolvement in Metamorphic $\text{In}_{0.83}\text{Ga}_{0.17}\text{As}/\text{InP}$ Photodetectors Through Ex-Situ Rapid Thermal Annealing. IEEE Journal of Quantum Electronics, 2022, 58, 1-7.	1.9	2
7	Effects of buffer doping on the strain relaxation of metamorphic InGaAs photodetector structures. Materials Science in Semiconductor Processing, 2020, 120, 105281.	4.0	0